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Team Nexperia



PNP resistor-equipped transistor; R1 = 2.2 kΩ, R2 = 10 kΩRev. 1 — 26 June 2012Product data s

Product data sheet

1. **Product profile**

1.1 General description

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC123YMB

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias transistors
- Reduces pick and place costs

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		3.6	4.5	5.5	



PNP resistor-equipped transistor; $R1 = 2.2 \text{ k}\Omega$, $R2 = 10 \text{ k}\Omega$

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)		
3	0	output (collector)	2 Transparent top view DFN1006B-3 (SOT883B)	1 R1 R2 R2 R2 R2 R2 R2 R2 R2 R2 R2 R2 R2 R2

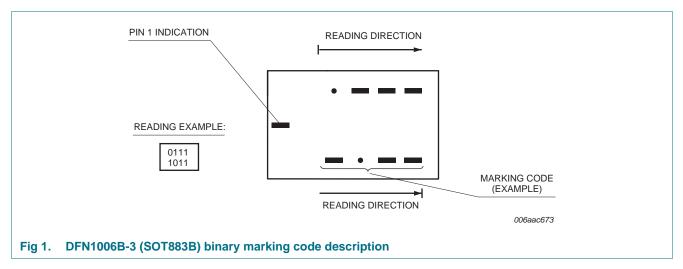
3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PDTA123YMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B		

4. Marking

Table 4.	Marking codes	
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Type number	Marking code
PDTA123YMB	0010 0100



PNP resistor-equipped transistor; $R1 = 2.2 \text{ k}\Omega$, $R2 = 10 \text{ k}\Omega$

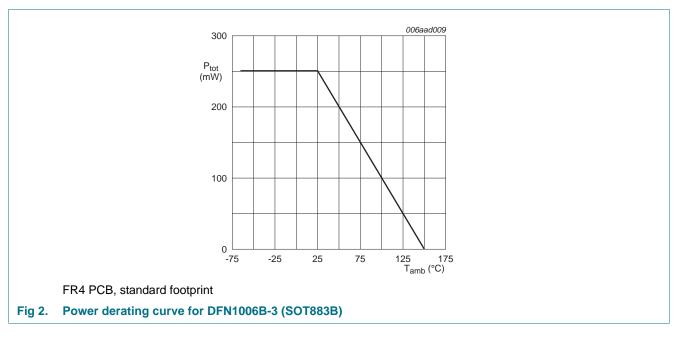
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
VI	input voltage	positive		-	5	V
		negative		-	-12	V
lo	output current			-	-100	mA
I _{CM}	peak collector current	pulsed; t _p ≤ 1 ms		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



6. Thermal characteristics

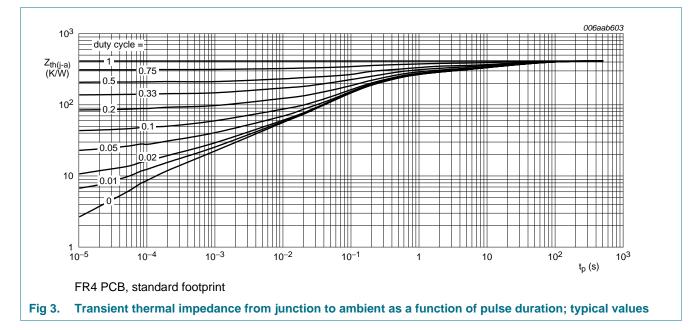
Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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PDTA123YMB

PNP resistor-equipped transistor; $R1 = 2.2 \text{ k}\Omega$, $R2 = 10 \text{ k}\Omega$



7. Characteristics

Table 7. Characteristics

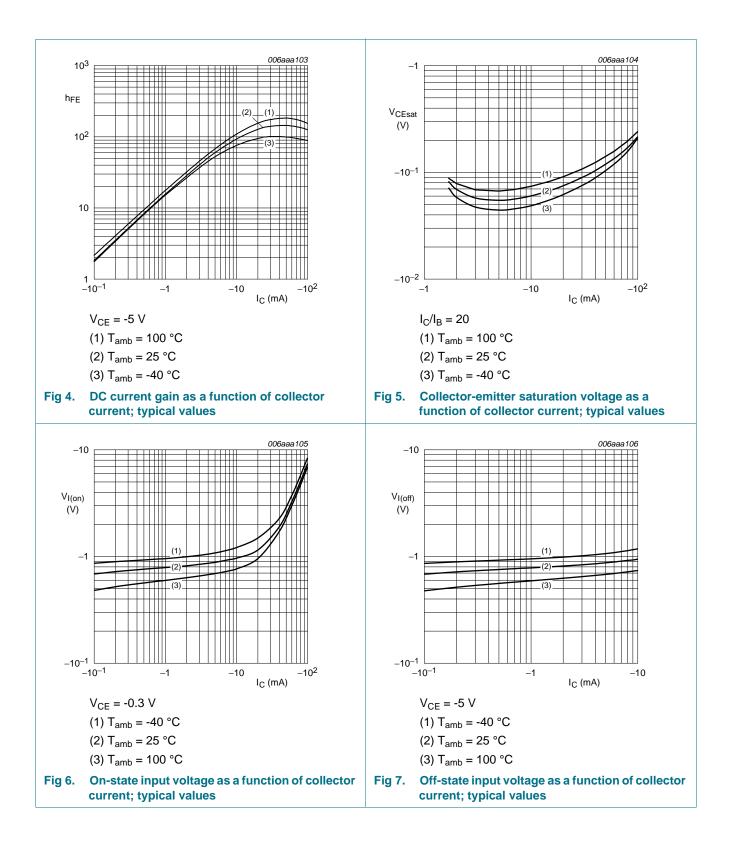
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
-					тур		
СВО	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$		-	-	-100	nA
CEO	collector-emitter cut-off	V_{CE} = -30 V; I_B = 0 A; T_{amb} = 25 $^\circ C$		-	-	-1	μA
	current	V_{CE} = -30 V; I _B = 0 A; T _j = 150 °C		-	-	-5	μA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	-700	μA
h _{FE}	DC current gain	V_{CE} = -5 V; I _C = -5 mA; T _{amb} = 25 °C		35	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -10 mA; I_{B} = -0.5 mA; T_{amb} = 25 °C		-	-	-150	mV
V _{I(off)}	off-state input voltage	V_{CE} = -5 V; I_{C} = -100 $\mu A;$ T_{amb} = 25 °C		-	-0.75	-0.3	V
V _{I(on)}	on-state input voltage	V_{CE} = -0.3 V; I_{C} = -20 mA; T_{amb} = 25 $^{\circ}C$		-2.5	-1.15	-	V
R1	bias resistor 1 (input)	T _{amb} = 25 °C		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio			3.6	4.5	5.5	
C _C	collector capacitance	V_{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	2	pF
f _T	transition frequency	V_{CE} = -5 V; I _C = -10 mA; f = 100 MHz; T _{amb} = 25 °C	<u>[1]</u>	-	180	-	MHz

[1] Characteristics of built-in transistor.

PDTA123YMB Product data sheet

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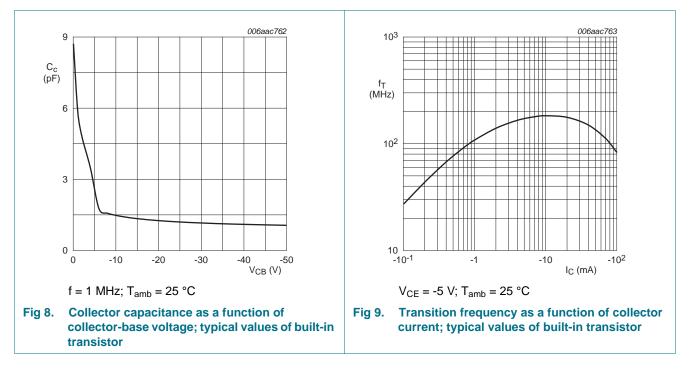
PNP resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 10 k Ω



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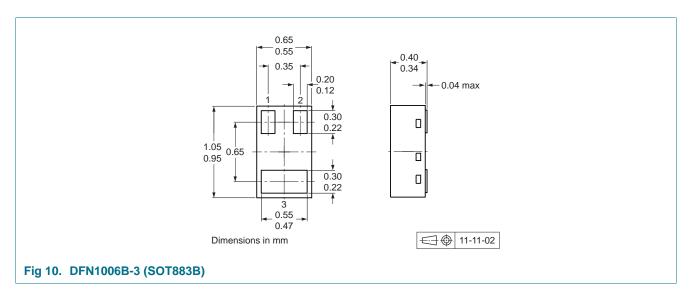
8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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Package outline 9.



10. Soldering

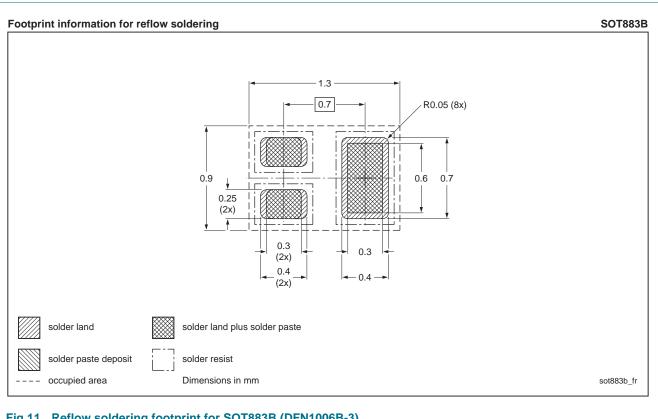


Fig 11. Reflow soldering footprint for SOT883B (DFN1006B-3)

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11. Revision history

Table 8. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA123YMB v.1	20120626	Product data sheet	-	-

PNP resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 10 k Ω

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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